Thickness Determination of Ultrathin Gate Oxide 
Grown by Wet Oxidation

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Current nano-devices require high-κ gate dielectrics and low-κ interlayer dielectrics. For these devices, the thickness of gate oxides is crucial for determining the device performance. In this study, we present a new method for determining the thickness of ultrathin gate oxides grown by wet oxidation. The method is based on the analysis of the dielectric constant and the oxide thickness. The results show that the method is accurate and reliable for determining the thickness of ultrathin gate oxides. This method can be applied to various types of devices, including SOI and FinFETs. Overall, the results of this study provide important insights into the design and fabrication of new nano-devices.